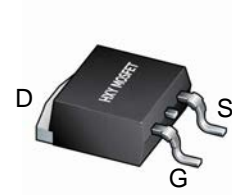




## Description

The STD25N10F7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



**TO-252-2L**

## General Features

$V_{DS} = 100V$   $I_D = 30A$

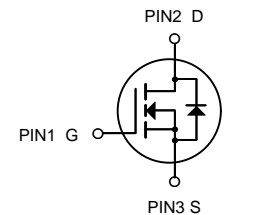
$R_{DS(ON)} < 48m\Omega @ V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STD25N10F7	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	13	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	80	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	30	mJ
$P_D @ T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	42	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	3.6	$^\circ C/W$



**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=10A$	-	37	48	m $\Omega$
		$V_{GS}=4.5V, I_D=6A$	-	39	55	m $\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	1964	-	pF
$C_{oss}$	Output Capacitance		-	90	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	74	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=80V, I_D=20A,$ $V_{GS}=4.5V$	-	20	-	nC
$Q_{gs}$	Gate-Source Charge		-	3.1	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	14	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=80V, I_D=20A,$ $R_G=3.1\Omega, V_{GS}=4.5V$	-	11	-	ns
$t_r$	Turn-on Rise Time		-	91	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	40	-	ns
$t_f$	Turn-off Fall Time		-	71	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	27	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=20A$	-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=20A,$ $di/dt=100A/\mu s$	-	64	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

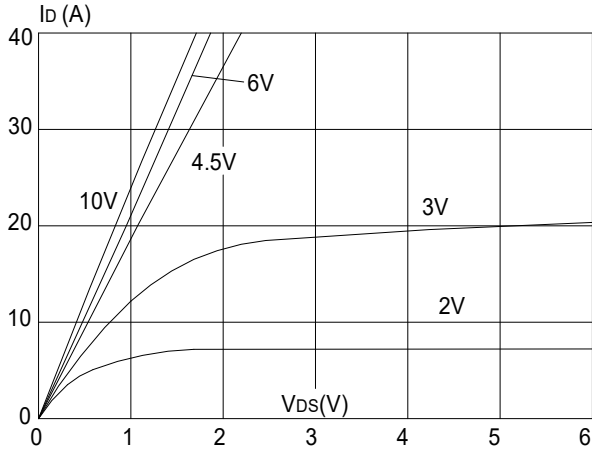
2. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}= 11A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

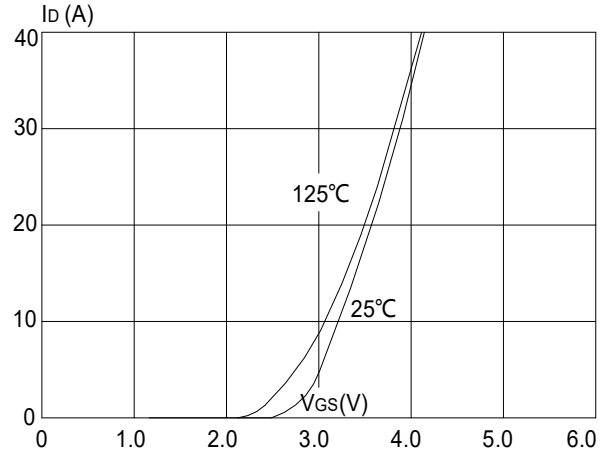


## Typical Performance Characteristics

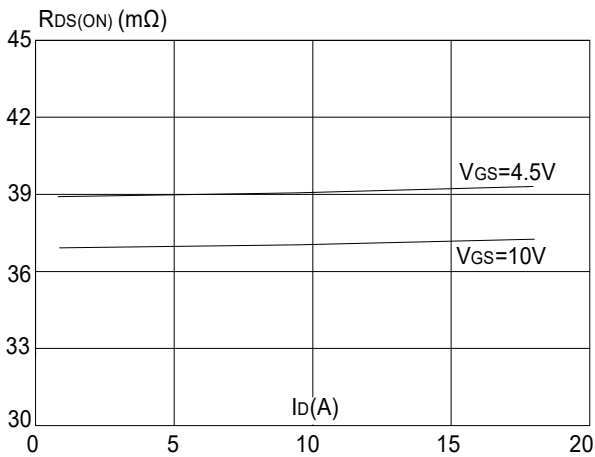
**Figure 1: Output Characteristics**



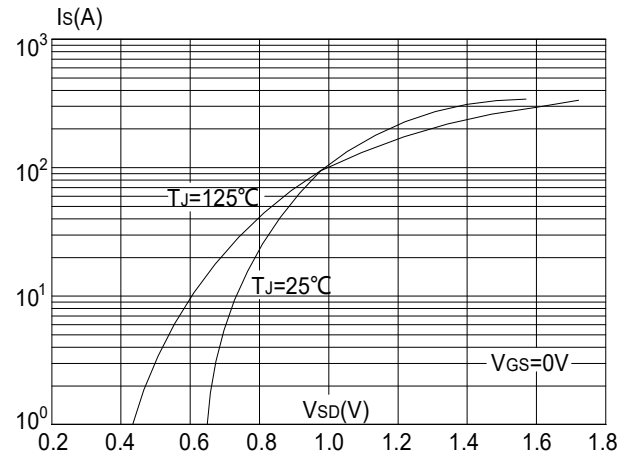
**Figure 2: Typical Transfer Characteristics**



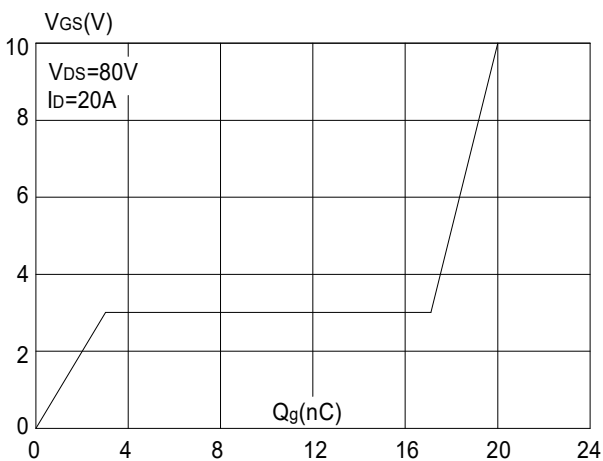
**Figure 3: On-resistance vs. Drain Current**



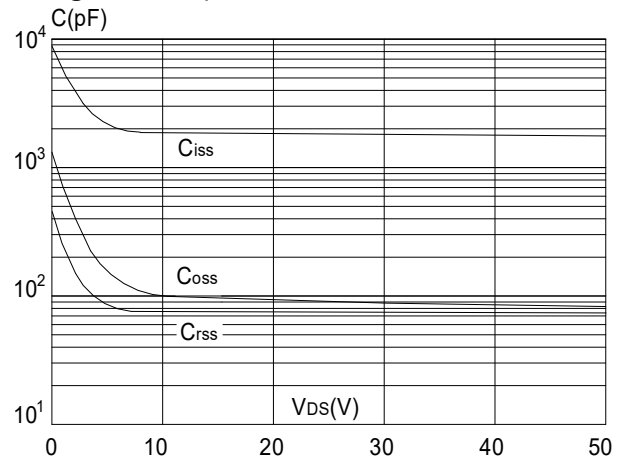
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

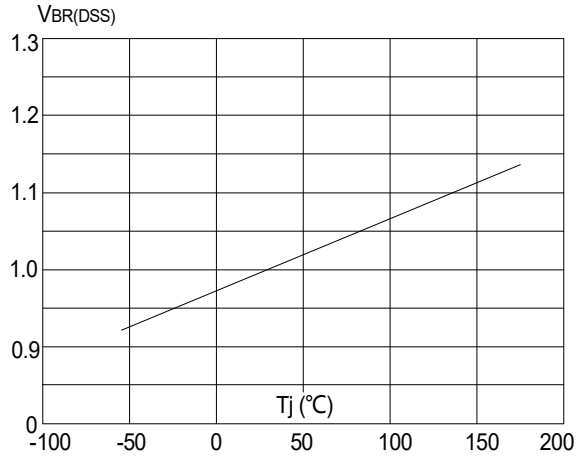


**Figure 6: Capacitance Characteristics**

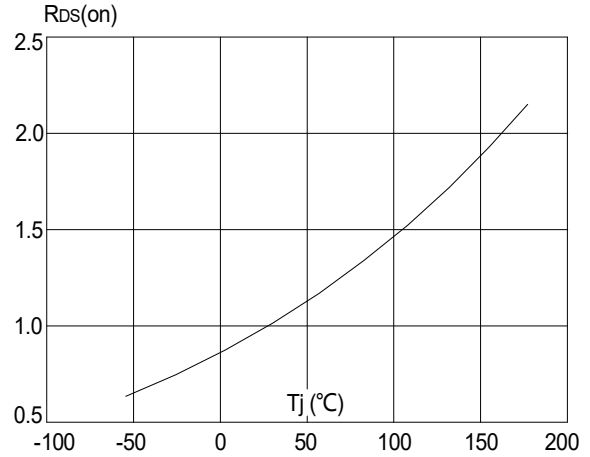




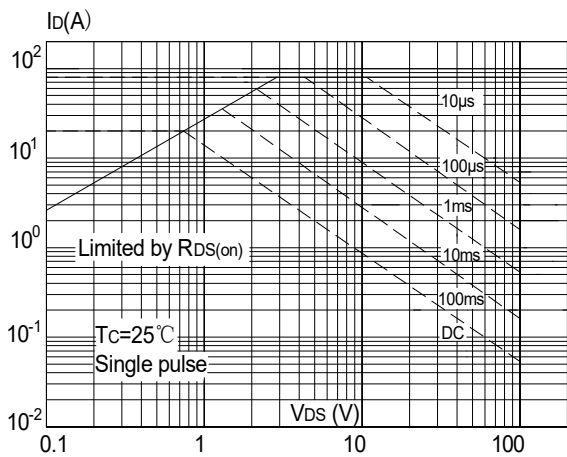
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



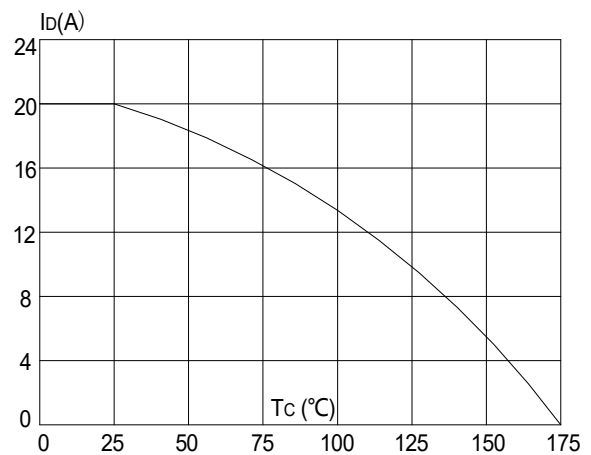
**Figure 8:** Normalized on Resistance vs. Junction Temperature



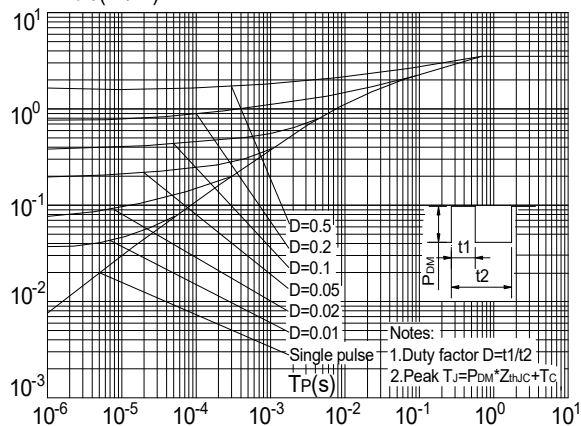
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

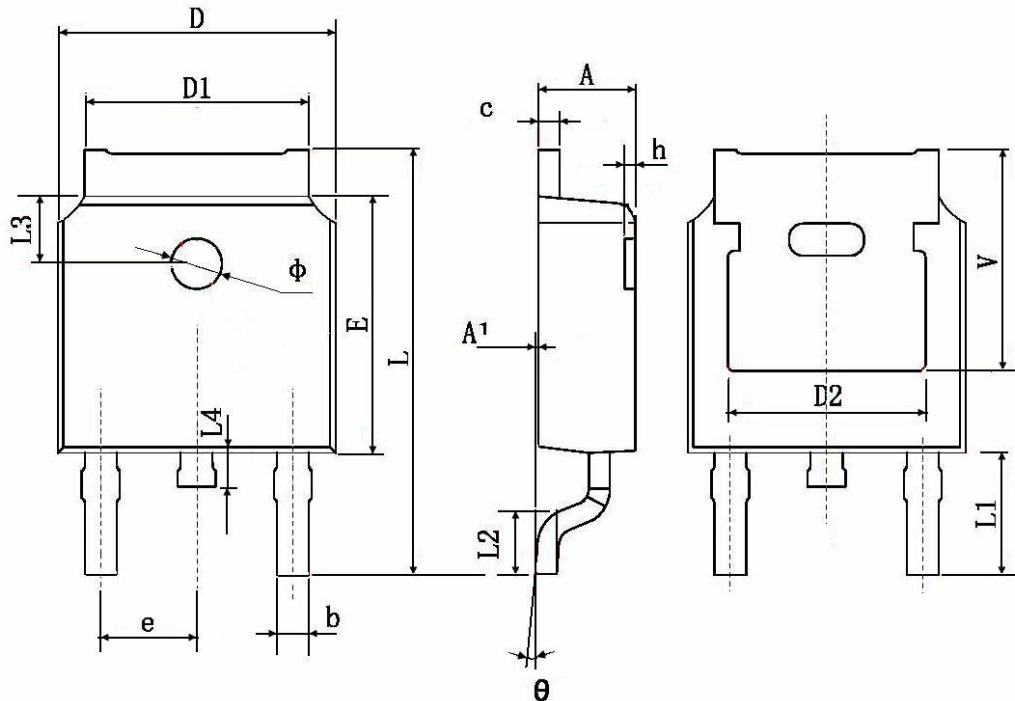


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





### TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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